## **Low Power Transistors**

## **NPN Silicon**

#### **Features**

- MIL-PRF-19500/391 Qualified
- Available as JAN, JANTX, and JANTXV

#### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	80	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	140	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	7.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	1.0	Adc
Total Device Dissipation @ T <sub>A</sub> = 25°C 2N3019, 2N3019S 2N3700	P <sub>T</sub>	800 500	mW
Total Device Dissipation @ T <sub>C</sub> = 25°C 2N3019, 2N3019S 2N3700	P <sub>T</sub>	5.0 1.0	W
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

#### THERMAL CHARACTERISTICS

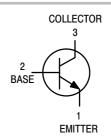
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient 2N3019, 2N3019S 2N3700	$R_{ hetaJA}$	195 325	°C/W
Thermal Resistance, Junction to Case 2N3019, 2N3019S 2N3700	$R_{ heta JC}$	30 150	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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2N3019



TO-39 CASE 205AB STYLE 1 2N3019S



TO-18 CASE 206AA STYLE 1 2N3700

#### **ORDERING INFORMATION**

Device	Package	Shipping
JAN2N3019		
JANTX2N3019	TO-5	Bulk
JANTXV2N3019		
JAN2N3019S		
JANTX2N3019S	TO-39	Bulk
JANTXV2N3019S		
JAN2N3700		
JANTX2N3700	TO-18	Bulk
JANTXV2N3700		

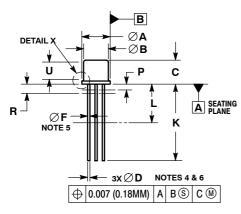
## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

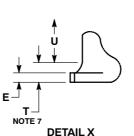
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u> </u>	1	1	ı
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 30 mAdc)	V <sub>(BR)CEO</sub>	80	_	Vdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 5.0 Vdc) (V <sub>EB</sub> = 7.0 Vdc)	I <sub>EBO</sub>	- -	10 10	nAdc μAdc
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 90 Vdc)	I <sub>CEO</sub>	-	10	nAdc
Collector–Base Cutoff Current (V <sub>CB</sub> = 140 Vdc)	I <sub>CBO</sub>	-	10	μAdc
ON CHARACTERISTICS (Note 1)	1			l .
DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=1.0 \text{ Adc, } V_{CE}=10 \text{ Vdc)} \end{array} $	h <sub>FE</sub>	50 90 100 50 15	300 - 300 300 -	-
Collector – Emitter Saturation Voltage ( $I_C$ = 150 mAdc, $I_B$ = 15 mAdc) ( $I_C$ = 500 mAdc, $I_B$ = 50 mAdc)	V <sub>CE(sat)</sub>	- -	0.2 0.5	Vdc
Base – Emitter Saturation Voltage (I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc)	V <sub>BE(sat)</sub>	-	1.1	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u> </u>		•	
Magnitude of Small–Signal Current Gain (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 10 Vdc, f = 20 MHz)	h <sub>fe</sub>	5.0	20	-
Small–Signal Current Gain ( $I_C = 1.0$ mAdc, $V_{CE} = 5$ Vdc, $f = 1$ kHz)	h <sub>fe</sub>	80	400	-
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz})$	C <sub>obo</sub>	-	12	pF
Input Capacitance ( $V_{EB} = 0.5 \text{ Vdc}, I_C = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$ )	C <sub>ibo</sub>	-	60	pF
Noise Figure ( $V_{CE}$ = 10 Vdc, $I_{C}$ = 100 $\mu$ Adc, $R_{g}$ = 1 $k\Omega$ , PBW = 200 Hz)	NF	-	4.0	dB
Collector–Base Time Constant (V <sub>CB</sub> = 10 Vdc, I <sub>C</sub> = 10 mAdc, f = 79.8 MHz)	r' <sub>b</sub> ,C <sub>C</sub>	-	400	ps
SWITCHING CHARACTERISTICS	-	•	•	•
Pulse Response (Reference Figure in MIL-PRF-19500/391)	t <sub>on</sub> + t <sub>off</sub>	-	30	ns
SWITCHING CHARACTERISTICS Pulse Response	t <sub>on</sub> + t <sub>off</sub>	_		ns

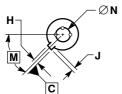
<sup>1.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

#### **PACKAGE DIMENSIONS**

TO-53-Lead CASE 205AA **ISSUE B** 



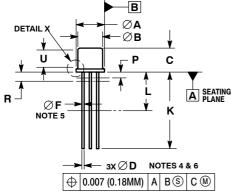


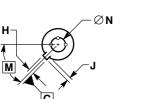


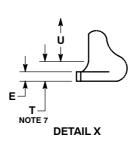


DETAIL

#### TO-39 3-Lead CASE 205AB **ISSUE A**









- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
- CONTROLLING DIMENSION: INCHES.
   DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
- LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.

- DIMENSION F APPLIES BETWEEN DIMENSION P AND L
  DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
  BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMEN-
- SIONS A, B, AND T.

  8. DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

	MILLIMETERS		ETERS INCHES	
DIM	MIN	MAX	MIN	MAX
Α	8.89	9.40	0.350	0.370
В	8.00	8.51	0.315	0.335
С	6.10	6.60	0.240	0.260
D	0.41	0.53	0.016	0.021
E	0.23	3.18	0.009	0.125
F	0.41	0.48	0.016	0.019
Н	0.71	0.86	0.028	0.034
J	0.73	1.02	0.029	0.040
K	38.10	44.45	1.500	1.750
L	6.35		0.250	
M	45°BSC		45 °BSC	
N	5.08 BSC		0.200 BSC	
P		1.27		0.050
R	1.37 BSC		0.054 BSC	
T		0.76		0.030
U	2.54		0.100	

STYLE 1:

PIN 1. EMITTER

- BASE
- COLLECTOR

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
- DIMENSION J MEASURED FROM DIAMETER A TO EDGE. LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE
- PLANE DEFINED BY DIMENSION R.
  DIMENSION F APPLIES BETWEEN DIMENSION P AND L.
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  DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

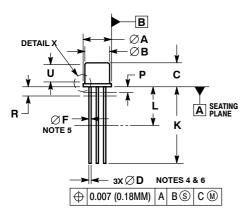
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	8.89	9.40	0.350	0.370
В	8.00	8.51	0.315	0.335
С	6.10	6.60	0.240	0.260
D	0.41	0.48	0.016	0.019
Е	0.23	3.18	0.009	0.125
F	0.41	0.48	0.016	0.019
Н	0.71	0.86	0.028	0.034
J	0.73	1.02	0.029	0.040
K	12.70	14.73	0.500	0.580
L	6.35		0.250	
M	45°	BSC	45°	BSC
N	5.08	BSC	0.200	BSC
P		1.27		0.050
R	1.37	1.37 BSC		BSC
T		0.76		0.030
U	2.54		0.100	

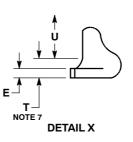
STYLE 1:

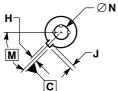
- PIN 1. EMITTER
  - BASE

#### PACKAGE DIMENSIONS

TO-18 3-Lead CASE 206AA **ISSUE A** 









DETAIL

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
   CONTROLLING DIMENSION: INCHES.
- CONTROLLING DIMENSION: INCHES.
- DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
  LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE
- PLANE DEFINED BY DIMENSION R.
  DIMENSION F APPLIES BETWEEN DIMENSION P AND L.

- DIMENSION D APPLIES BETWEEN DIMENSION L AND K. BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMEN-SIONS A, B, AND T.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	5.31	5.84	0.209	0.230
В	4.52	4.95	0.178	0.195
С	4.32	5.33	0.170	0.210
D	0.41	0.53	0.016	0.021
Е		0.76		0.030
F	0.41	0.48	0.016	0.019
Н	0.91	1.17	0.036	0.046
J	0.71	1.22	0.028	0.048
K	12.70	19.05	0.500	0.750
L	6.35		0.250	
M	45°	BSC	45°	BSC
N	2.54	BSC	0.100	BSC
Р		1.27		0.050
R	1.37 BSC		0.054 BSC	
T		0.76		0.030
U	2.54		0.100	

STYLE 1:

PIN 1. EMITTER

BASE

COLLECTOR

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